

N-Channel MOSFET

Description

The PSM6N03R6L uses split gate trench technology to provide excellent $R_{\text{DS(ON)}}$ and low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

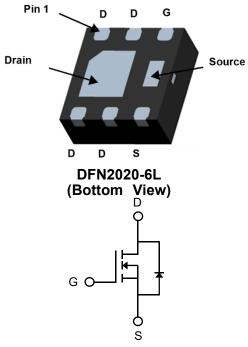
MOSFET Product Summary			
V _{DS} (V)	$R_{DS(on)}(m\Omega)(Typ)$	I _D (A)	
30	4.7@ V _{GS} = 10V	23	
	6.8@ V _{GS} = 4.5V	23	

Feature

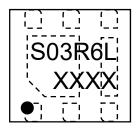
- ➤ Low R_{DS(ON)} Ensures On-State Losses are Minimized
- ➤ Excellent Q_{gd} x R_{DS(ON)} Product(FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- > 100% UIS (Avalanche) Rated
- ➤ Lead-Free Finish; RoHS Compliant
- > Halogen and Antimony Free. "Green" Device

Applications

- PWM applications
- Load switch
- Power management
- > DC-DC Converters
- Wireless Chargers



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous ¹⁾	T _C =25°C		23	А
Diam Current-Continuous	T _C =100°C	l _D	14.6	
Pulsed Drain Current ²⁾		I _{DM}	92	Α
Total Power Dissipation ³⁾		P_{D}	4.6	W
Avalanche Current ⁴⁾		I _{AS}	16	Α
Avalanche Energy ⁴⁾		E _{AS}	67	mJ
Thermal Resistance , Junction-to-Case ⁵⁾		$R_{\theta JC}$	12.3	°C/W
Thermal Resistance Junction-to-Ambient ⁶)	$R_{\theta JA}$	61.8	°C/W
Junction and Storage Temperature Range		$T_{J,}T_{STG}$	-55~+150	°C

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_{D} = 250\mu A$	30	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1.0	μA	
Gate-Body Leakage Current	I _{GSS}	$V_{GS} = \pm 20 \text{V}, V_{DS} = 0 \text{V}$	-	-	±100	nA	
On Characteristics							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0	1.5	2.0	V	
Drain-Source On-State Resistance	D	V _{GS} = 10V,I _D = 8A -		4.7	6.0		
	$R_{DS(ON)}$	V _{GS} = 4.5V,I _D = 6A	-	6.8	9.0	mΩ	
Dynamic Characteristics ⁷⁾							
Input Capacitance	C _{lss}		-	820	-	pF	
Output Capacitance	C _{oss}	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	-	216	-		
Reverse Transfer Capacitance	C _{rss}		-	15	-		
Switching Characteristics ⁷⁾	Switching Characteristics ⁷⁾						
Turn-on Delay Time	t _{d(on)}		-	5.0	-		
Turn-on Rise Time	t _r	V _{DS} = 15V, V _{GS} = 10V,	-	6.0	-		
Turn-Off Delay Time	t _{d(off)}	$R_G = 10\Omega, I_D = 10A$	-	33	-	ns	
Turn-Off Fall Time	t _f		-	17	-		
Total Gate Charge	Q_g		-	12.4	-		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15V, V_{GS} = 10V,$ $I_{D} = 10A$	-	1.7	-	nC	
Gate-Drain Charge	Q_{gd}		-	3.9	-		
Gate Resistance	R_g	f=1MHz, Open Drain	-	4.0	-	Ω	
Drain-Source Diode Characteristics							
Diode Forward Voltage	V _{SD}	V _{GS} = 0V,I _S = 1A	-	0.7	1.2	V	

Notes:

- $Computed \ continuous \ current \ assumes \ the \ condition \ of \ T_{J_Max} \ while \ the \ actual \ continuous \ current \ depends \ on \ the \ thermal \ \& \ electro-mechanical \ application$

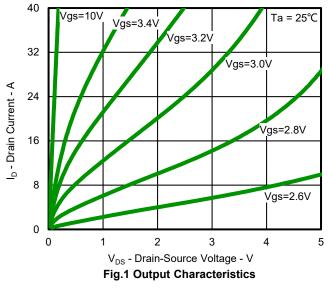
- poard design.

 Repetitive Rating: Pulse width limited by maximum junction temperature(T_{J_Max}=150°C).

 Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

 This single-pulse measurement was taken under the following condition (L=0.1mH,V_{GS}=10V,V_{DS}=30V)while it's value is limited by T_{J_Max}=150°C.
- Device mounted on infinite heatsink.
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
- Guaranteed by design, not subject to production.

Typical Characteristics



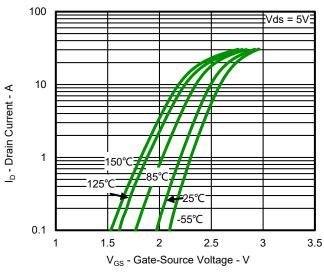
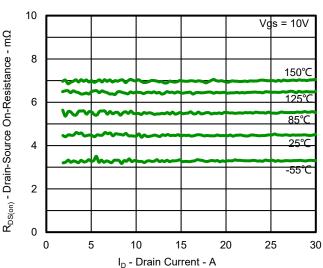


Fig.2 Typical Transfer Characteristic



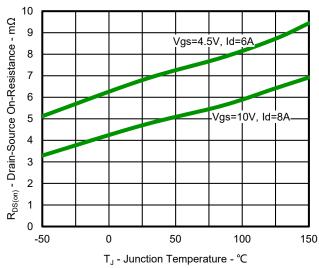
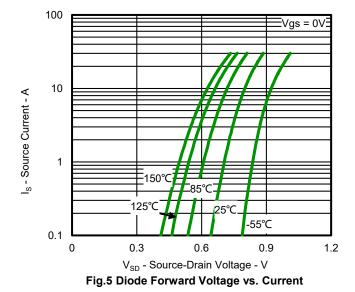


Fig.3 Typical On-Resistance vs Drain Current and Temperature





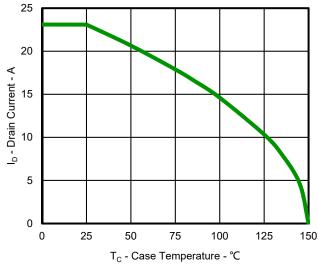
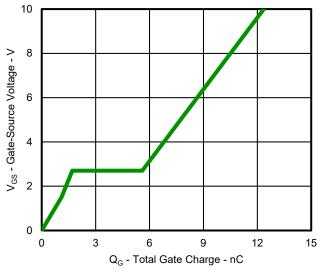


Fig.6 Maximum Drain Current vs. Case Temperature

N-Channel MOSFET

PSM6N03R6L



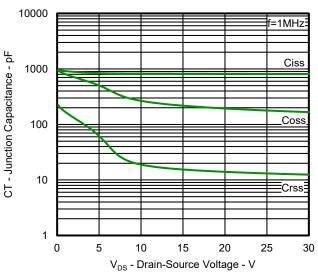


Fig.7 Gate Charge Characteristics

Fig.8 Typical Junction Capacitance

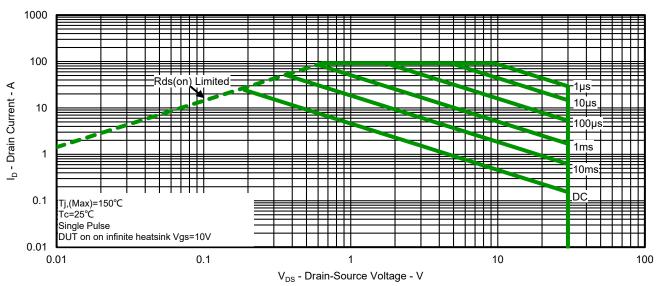


Fig.9 Safe Operation Area

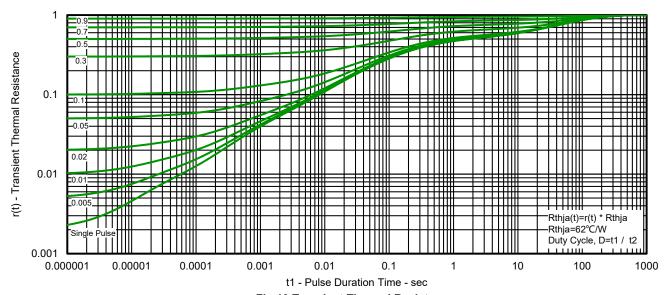
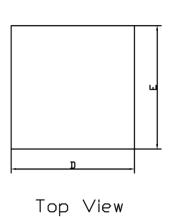
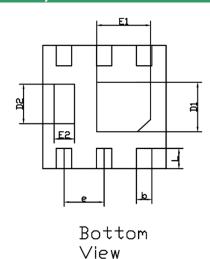
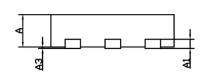


Fig.10 Transient Thermal Resistance

Product Dimension (DFN2020-6L)



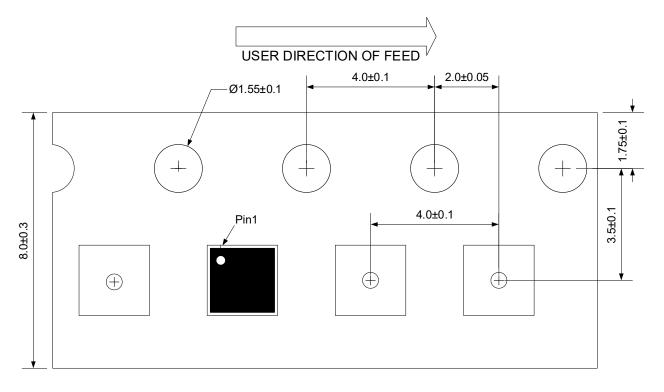




Side View

Dim	Millin	neters	Inches		
Dim	Min	Max	Min	Max	
Α	0.50	0.60	0.020	0.024	
A1	0.15 Ref.		0.006 Ref.		
А3	0.00	0.05	0.000	0.002	
D	1.95	2.05	0.077	0.081	
Е	1.95	2.05	0.077	0.081	
D1	0.875	0.925	0.034	0.036	
D2	0.675	0.725	0.027	0.029	
E1	0.875	0.925	0.034	0.036	
E2	0.275	0.325	0.011	0.013	
b	0.30 Ref.		0.012 Ref.		
е	0.65 Ref.		0.026 Ref.		
L	0.25	0.35	0.010	0.014	

Load with information



Unit:mm

Ordering information

Package	Reel	Shipping
DFN2020-6L	7"	3000 / Tape & Reel

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